PATENT

PROCESS FOR THE TREATMENT OF SUBSTRATES FOR MICROELECTRONICS AND SUBSTRATES OBTAINED BY THIS PROCESS

Applicant: S.O.I.TEC SILICON ON INSULATOR TECHNOLOGIES

ABSTRACT

The invention relates to a process for the treatment of substrates (1) for microelectronics or optoelectronics comprising a working layer (6) at least partially composed of an oxidizable material on at least one of their faces, this process comprising:

- a first sacrificial oxidation stage for removing material constituting the working layer (6) over a certain surface thickness of each substrate (1),
- a stage of polishing (200) the face which has been subjected to the first sacrificial oxidation stage (100), and
- a second sacrificial oxidation stage for again removing material constituting the working layer (6) on the polished face (17).

FIGURE 1



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